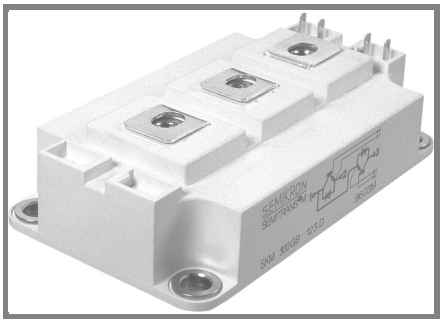
SKM 300GB174D



SEMITRANS^{TM} 3

Low Loss IGBT Modules

SKM 300GB174D

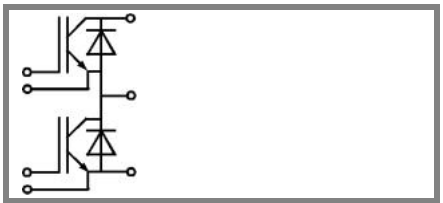
Preliminary Data

Features

- N channel, homogeneous Silicon structure (NPT - Non punch-trough IGBT)
- Low inductance case
- High short circuit capability, self limiting
- Fast & soft inverse CAL diodes
- Without hard mould
- Isolated copper baseplate using DCB Direct Copper Bonding
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications

- AC inverter drives on mains 575 - 750 V_{AC}
- DC bus voltage 750 - 1200 V_{DC}
- Public Transport (auxiliary syst.)
- Switching (not for linear use)



GB

Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1700	V
I_C	T_c = 25 (80) °C	320 (230)	A
I_{CRM}	t_p = 1 ms	400	A
V_{GES}		± 20	V
T_{vj}, (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	3400	V
Inverse diode			
I_F	T_c = 25 (80) °C	390 (260)	A
I_{FRM}	t_p = 1 ms	400	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	2200	A

Characteristics	T_c = 25 °C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 9 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25 () °C		0,1	0,3	mA
$V_{CE(TO)}$	T_j = 25 () °C		1,35 (1,5)	1,65 (1,8)	V
r_{CE}	V_{GE} = 20 V, T_j = 25 (125) °C		7,25 (8,75)	8,25 (10)	mΩ
$V_{CE(sat)}$	I_{Cnom} = 200 A, V_{GE} = 15 V, chip level		2,7 (3,25)	3,2 (3,8)	V
C_{ies}	under following conditions		14		nF
C_{oes}	V_{GE} = 0, V_{CE} = 25 V, f = 1 MHz		2		nF
C_{res}			0,6		nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip T_c= 25 (125) °C		0,35 (0,5)		mΩ
$t_{d(on)}$	V_{CC} = 1200 V, I_{Cnom} = 200 A		100		ns
t_r	R_{Gon} = R_{Goff} = 6,8 Ω, T_j = 125 °C		100		ns
$t_{d(off)}$	V_{GE} = ± 15 V		900		ns
t_f			150		ns
E_{on} (E_{off})			125 (95)		mJ
Inverse diode					
V_F = V_{EC}	I_{Fnom} = 200 A; V_{GE} = 0 V; T_j = 25 (125) °C		2,15 (1,9)	2,4 (2,25)	V
$V_{(TO)}$	T_j = 125 () °C		1,3	1,5	V
r_T	T_j = 125 () °C		3	4	mΩ
I_{RRM}	I_{Fnom} = 200 A; T_j = 25 (125) °C		100 (200)		A
Q_{rr}	di/dt = A/µs		24 (50)		µC
E_{rr}	V_{GE} = V		10 (18)		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,07	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,125	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6				Nm
w				325	g

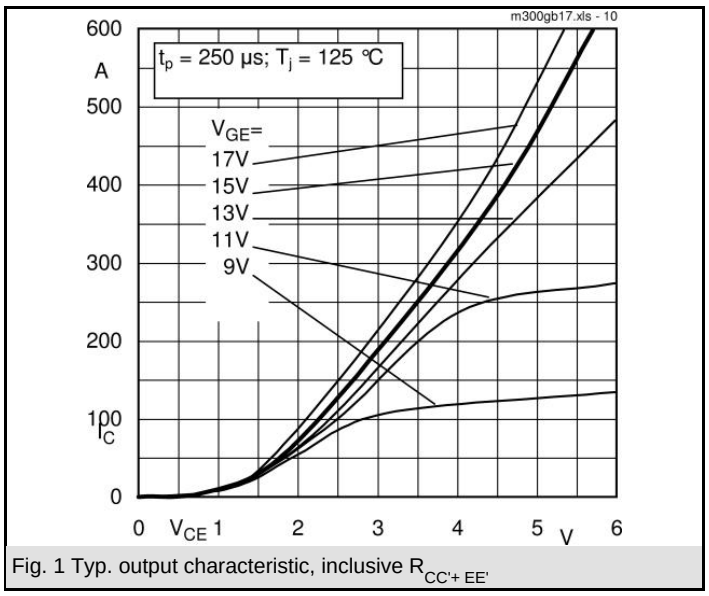


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

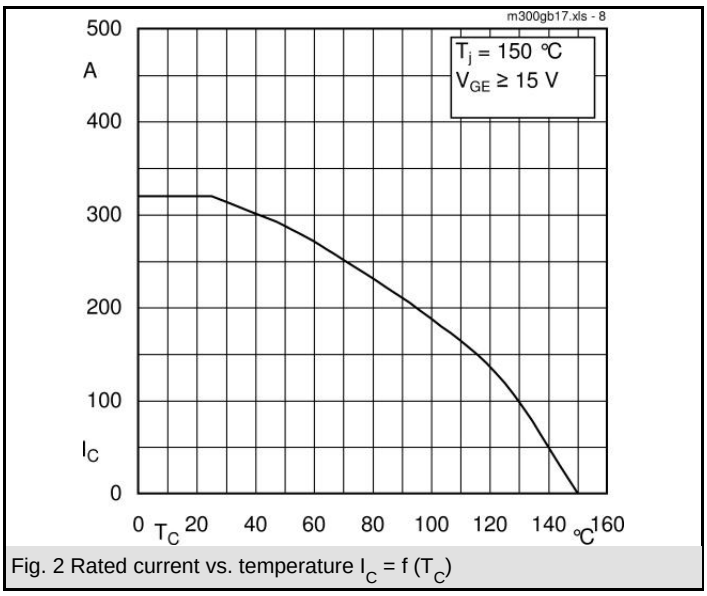


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

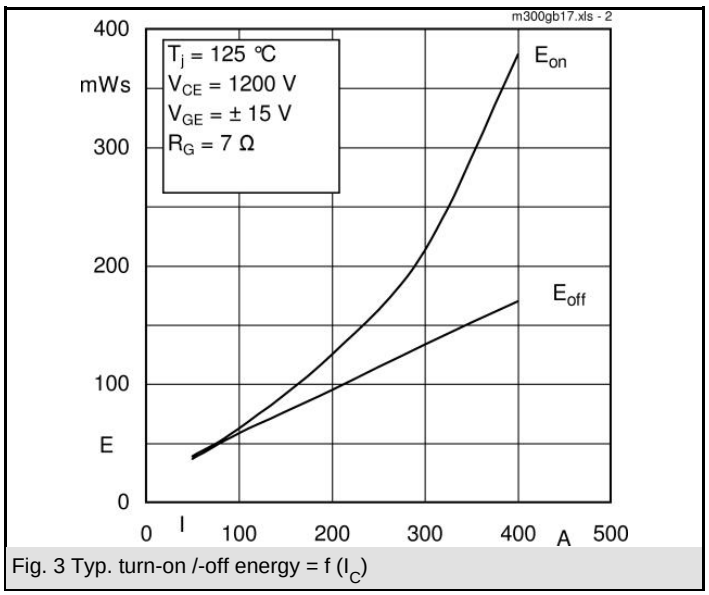


Fig. 3 Typ. turn-on /-off energy = f (I_C)

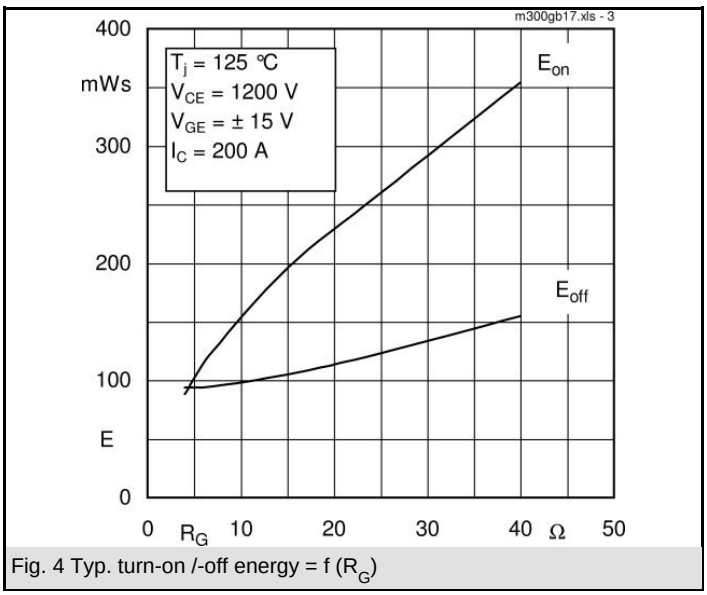


Fig. 4 Typ. turn-on /-off energy = f (R_G)

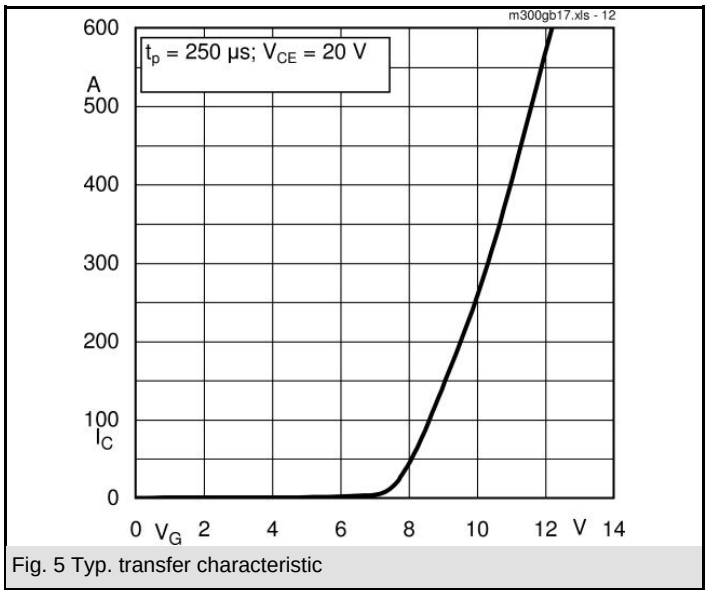


Fig. 5 Typ. transfer characteristic

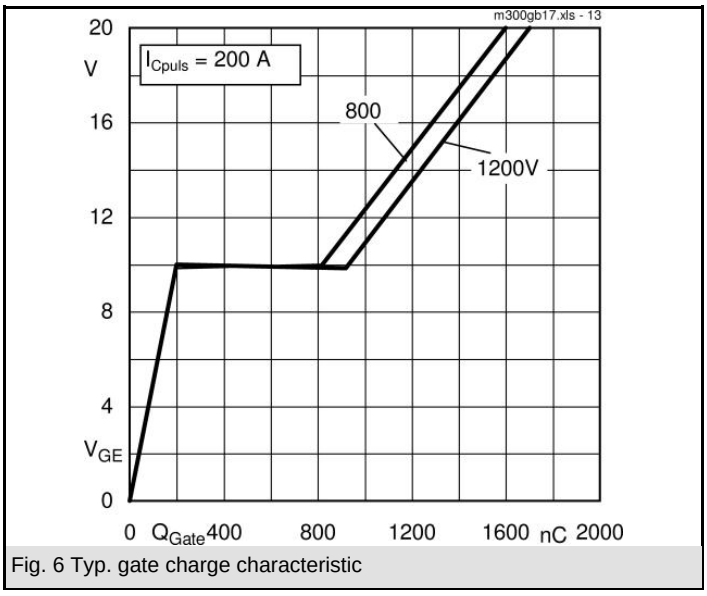


Fig. 6 Typ. gate charge characteristic

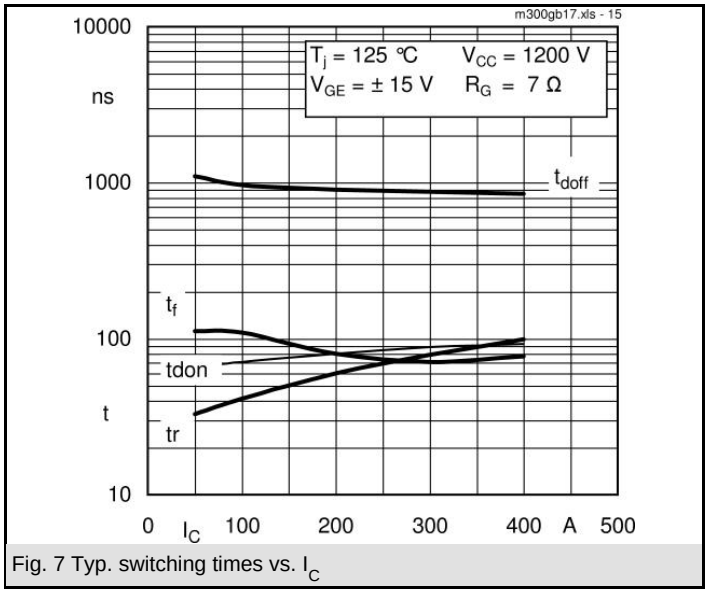


Fig. 7 Typ. switching times vs. I_C

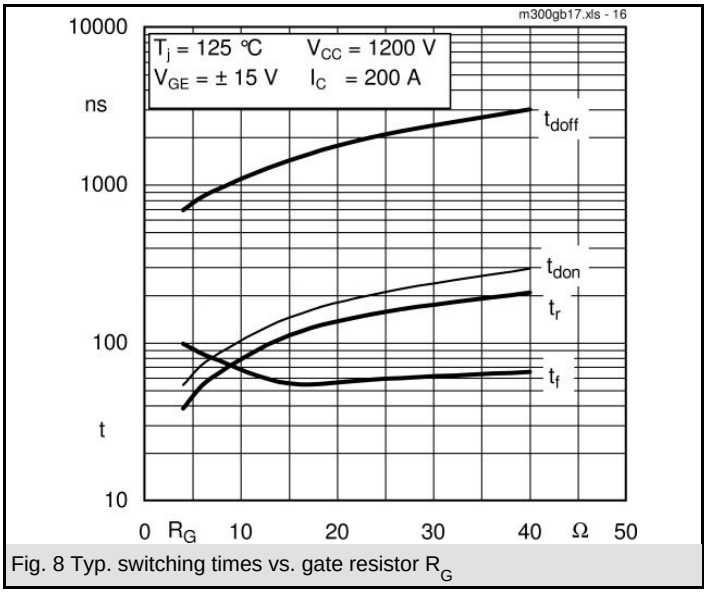


Fig. 8 Typ. switching times vs. gate resistor R_G

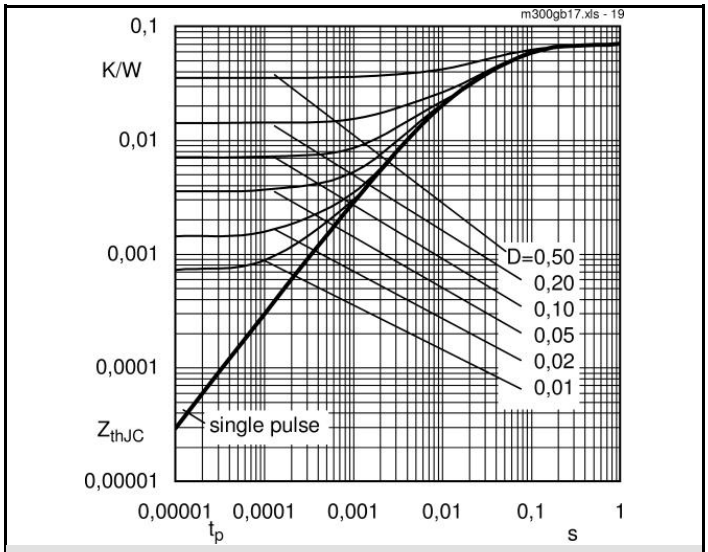


Fig. 9 Transient thermal impedance of IGBT

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

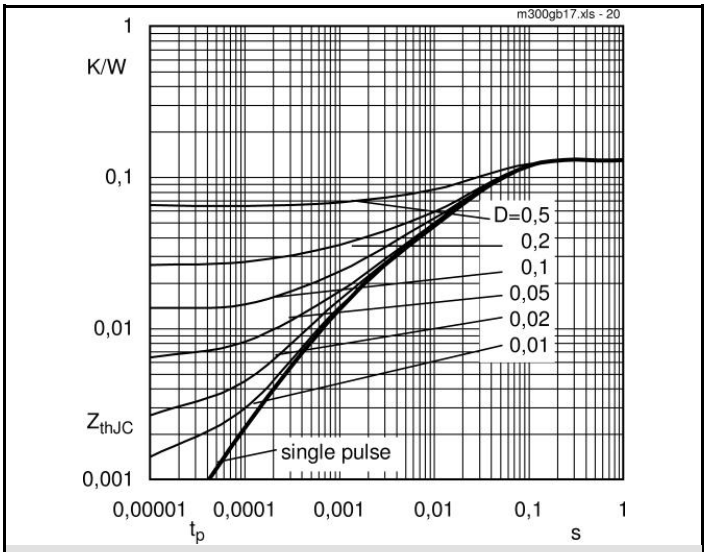


Fig. 10 Transient thermal impedance of FWD

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

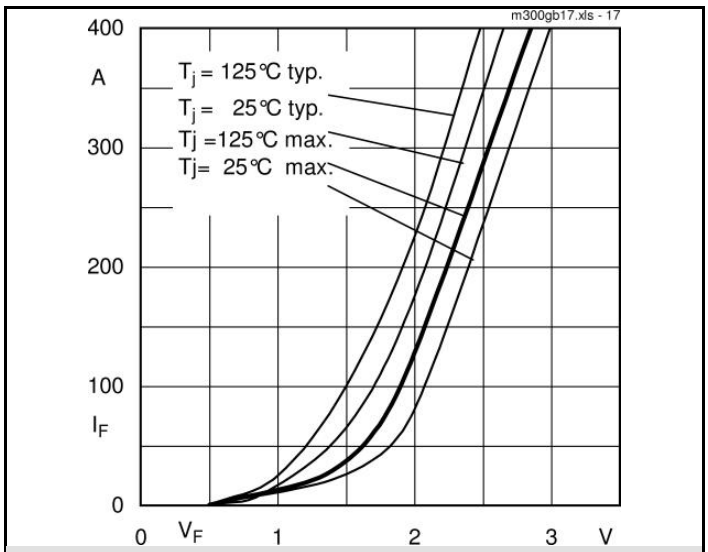


Fig. 11 CAL diode forward characteristic

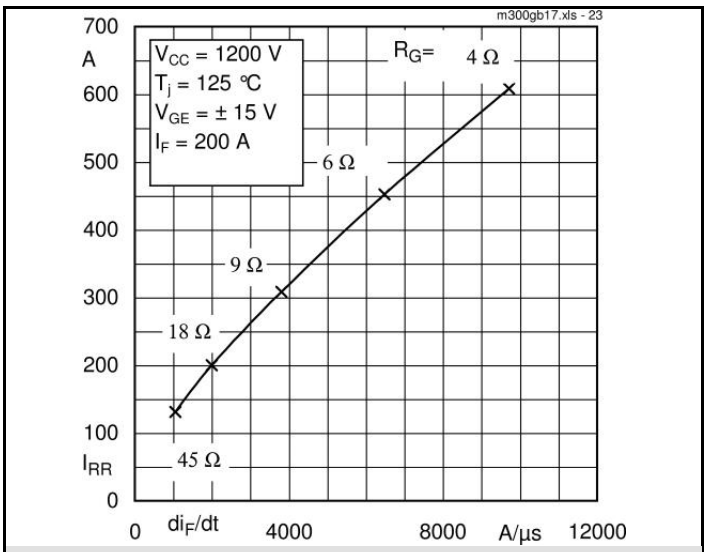


Fig. 12 Typ. CAL diode peak reverse recovery current

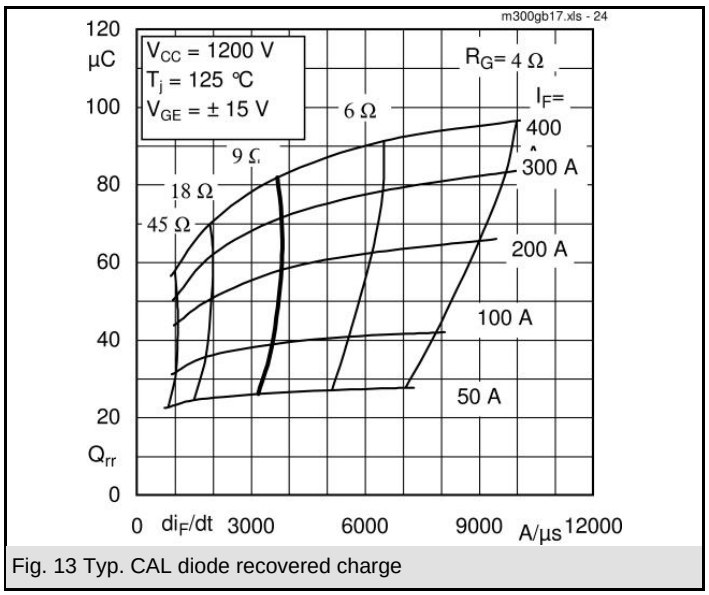
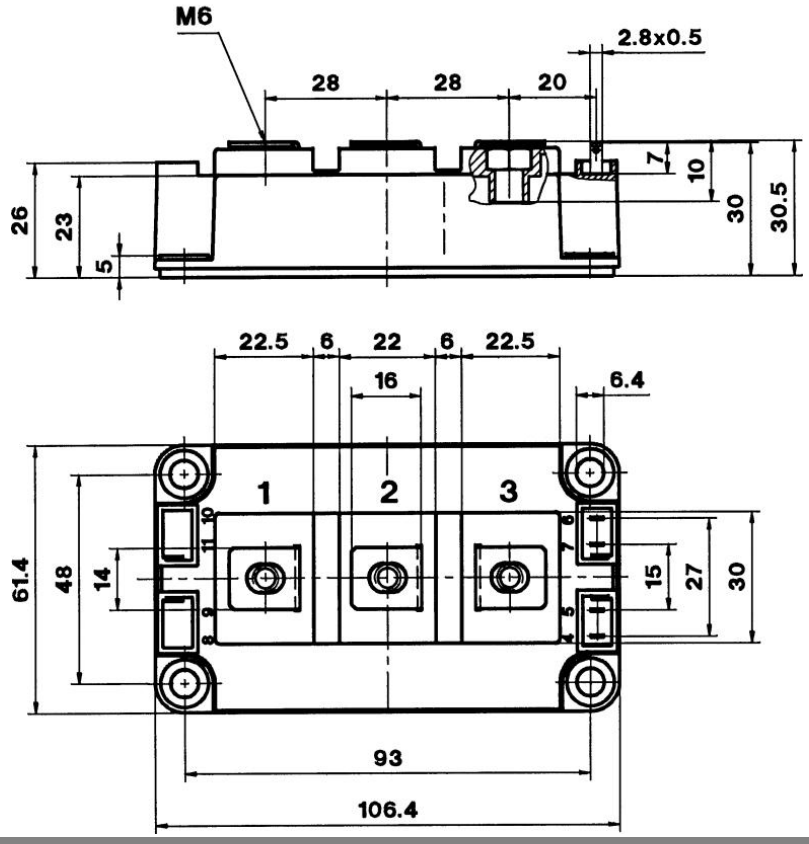


Fig. 13 Typ. CAL diode recovered charge

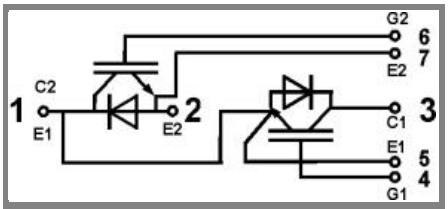
UL Recognized
File no. E 63 532

Dimensions in mm

CASED56



Case D 56



GB Case D 56

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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